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Kind regards,

Team Nexperia

# PMZB380XN

30 V, single N-channel Trench MOSFET

1 August 2012

Product data sheet

## 1. Product profile

### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile of 0.37mm height

### 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	-	30	V
$V_{GS}$	gate-source voltage			-12	-	12	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-	930	mA
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 200\text{ mA}; T_j = 25\text{ }^{\circ}\text{C}$		-	0.38	0.46	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

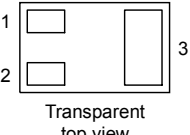
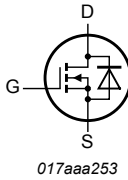


Scan or click this QR code to view the latest information for this product



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view <b>DFN1006B-3 (SOT883B)</b>	 017aaa253
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB380XN	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB380XN	0000 1001

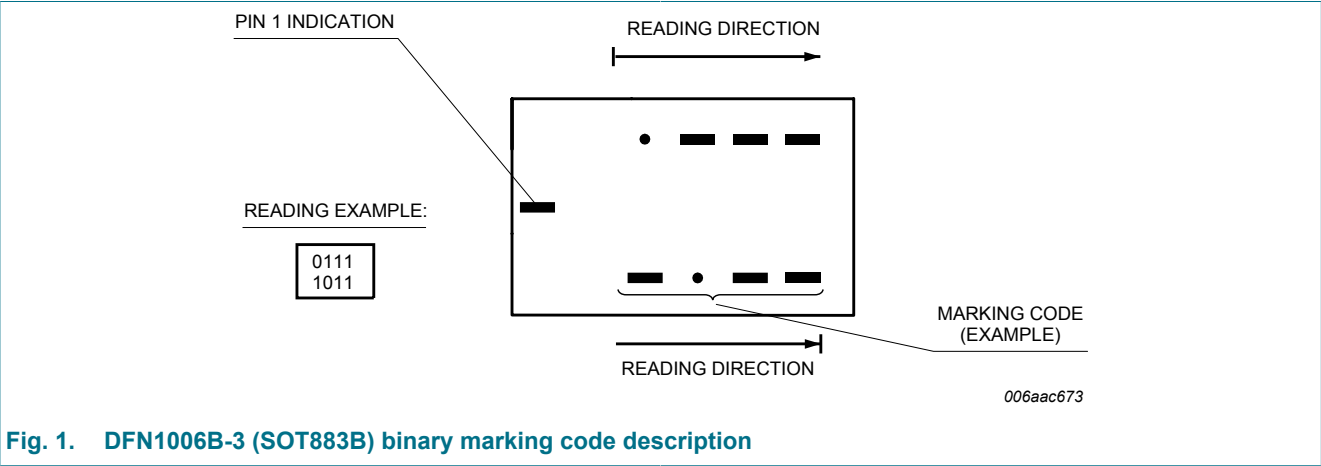


Fig. 1. DFN1006B-3 (SOT883B) binary marking code description

## 5. Limiting values

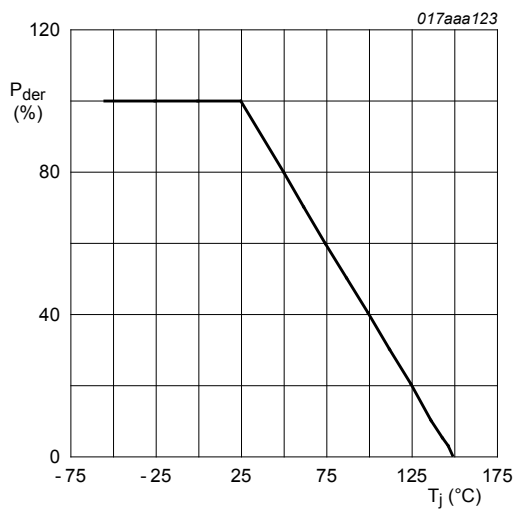
**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	930	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	590	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	3.7	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	670	mA

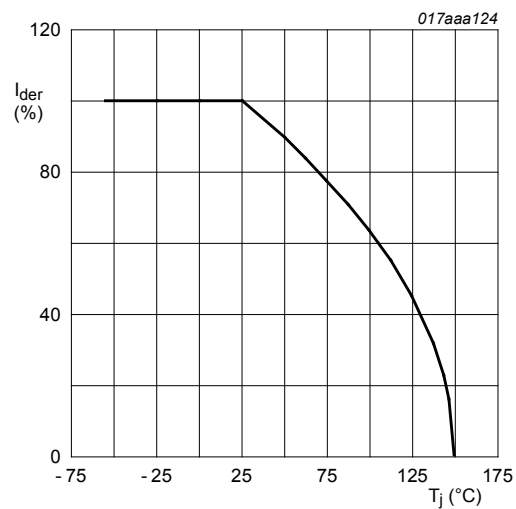
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



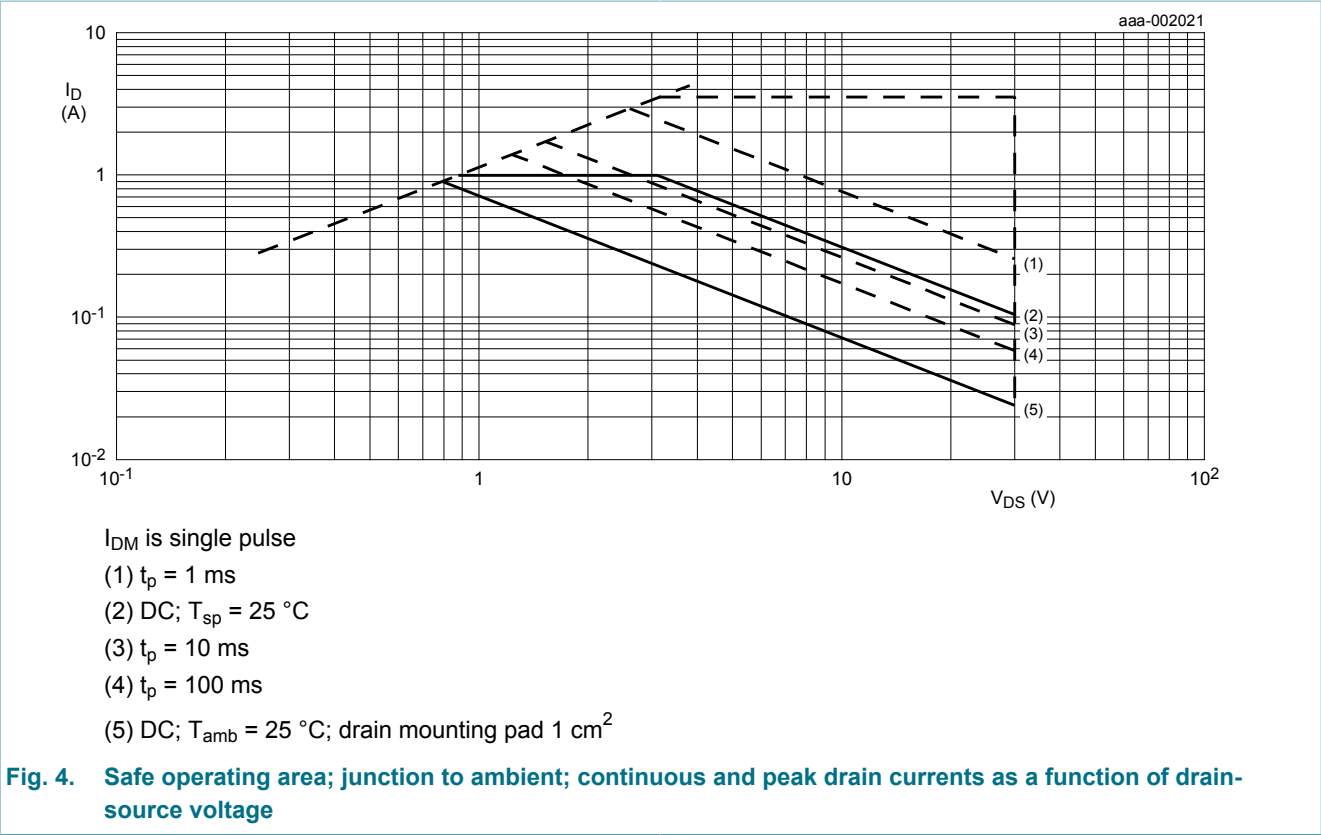
**Fig. 2. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 3. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



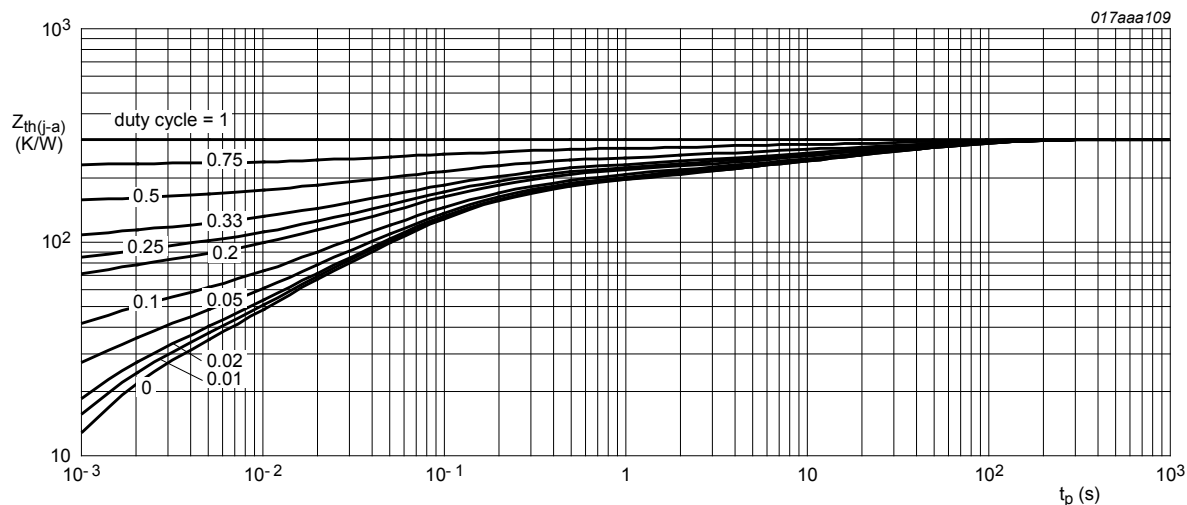
6. Thermal characteristics

Table 6. Thermal characteristics

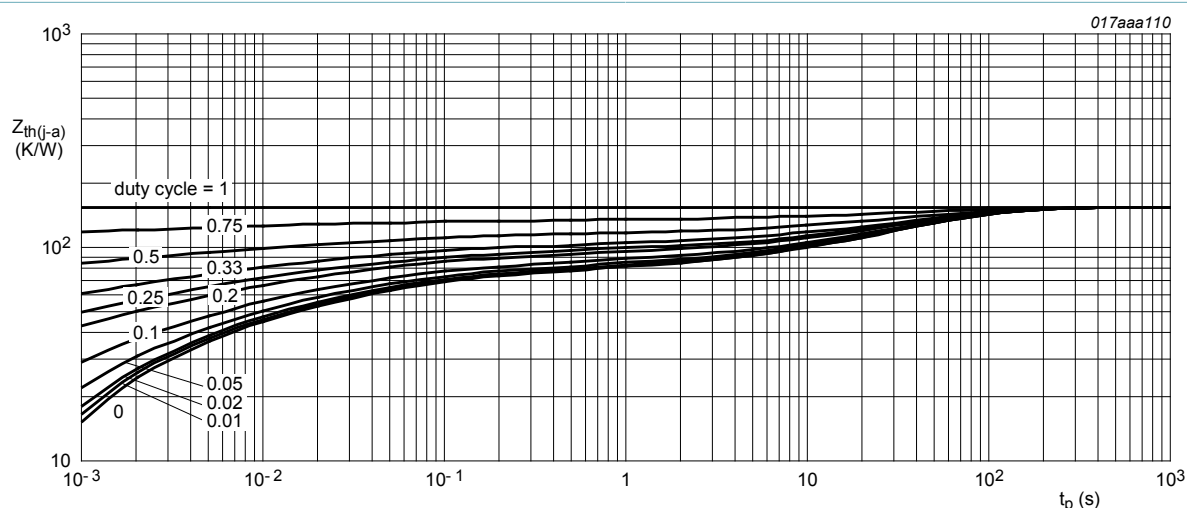
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .



FR4 PCB, standard footprint

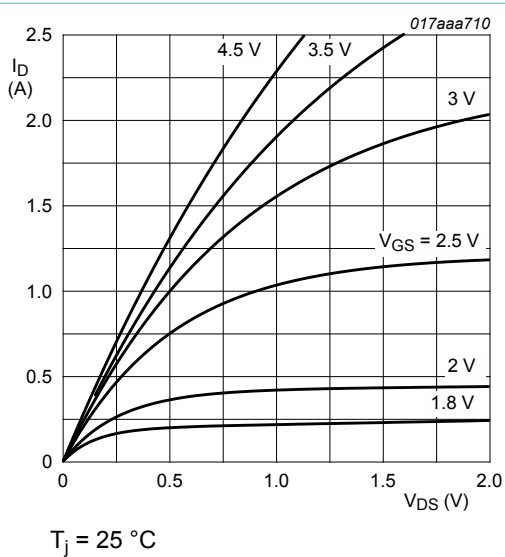
**Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>
**Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

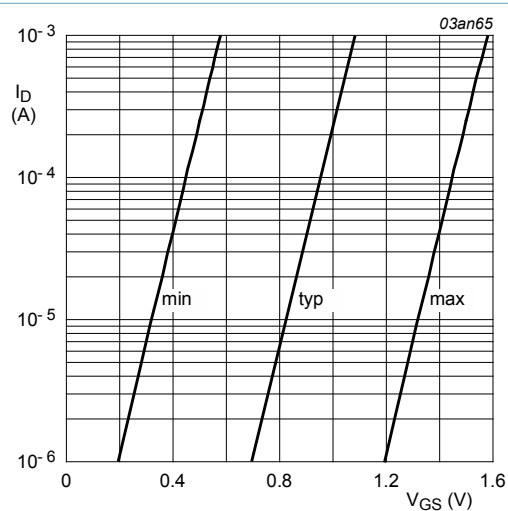
**Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25^\circ C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25^\circ C$	0.5	1	1.5	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V$ ; $V_{GS} = 0 V$ ; $T_j = 25^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 30 V$ ; $V_{GS} = 0 V$ ; $T_j = 150^\circ C$	-	-	100	$\mu A$

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	0.1	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	0.1	μA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C		-	0.38	0.46	Ω
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C		-	0.57	0.7	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C		-	0.55	0.68	mΩ
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C		-	1300	-	mS
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 1 A; V <sub>GS</sub> = 4.5 V; T <sub>j</sub> = 25 °C		-	0.65	0.87	nC
Q <sub>GS</sub>	gate-source charge			-	0.14	-	nC
Q <sub>GD</sub>	gate-drain charge			-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; f = 1 MHz; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	37	56	pF
C <sub>oss</sub>	output capacitance			-	8.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	5.4	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; R <sub>L</sub> = 15 Ω; V <sub>GS</sub> = 4.5 V; R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C		-	6.5	13	ns
t <sub>r</sub>	rise time			-	9.5	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	14	28	ns
t <sub>f</sub>	fall time			-	5.5	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 300 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.78	1.2	V



**Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values**



**Fig. 8. Subthreshold drain current as a function of gate-source voltage**

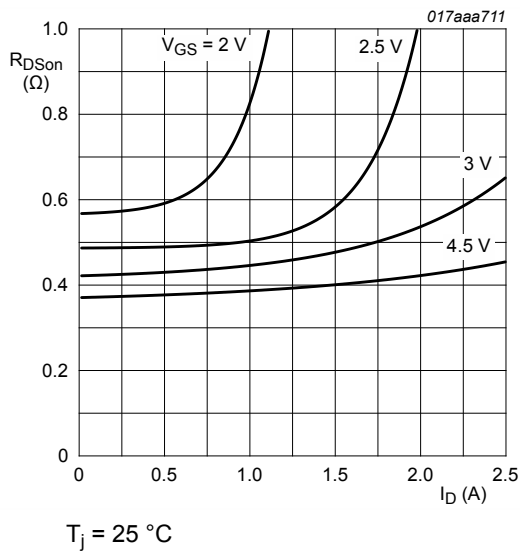


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

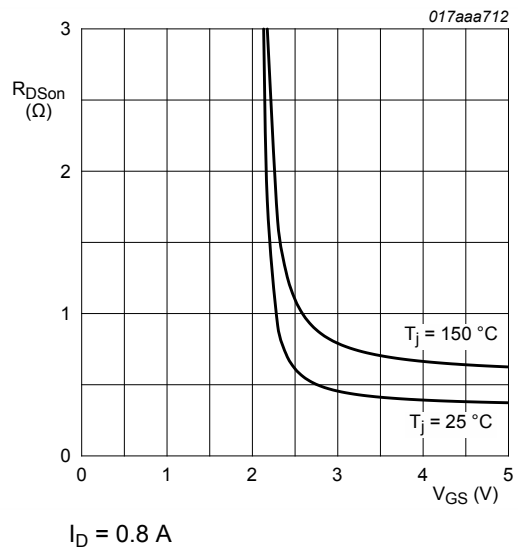


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

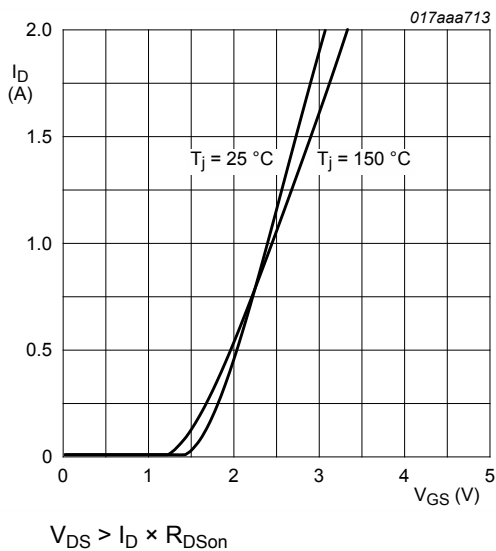


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

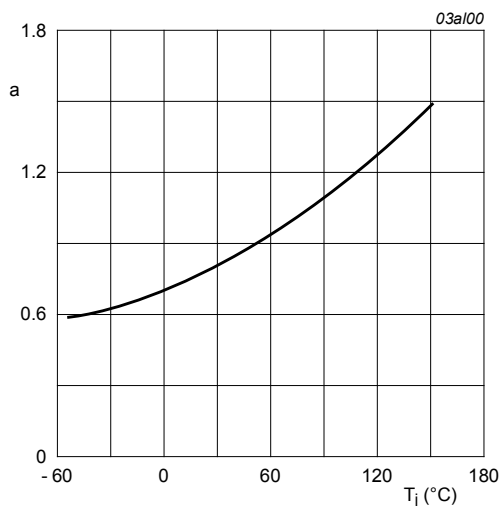


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

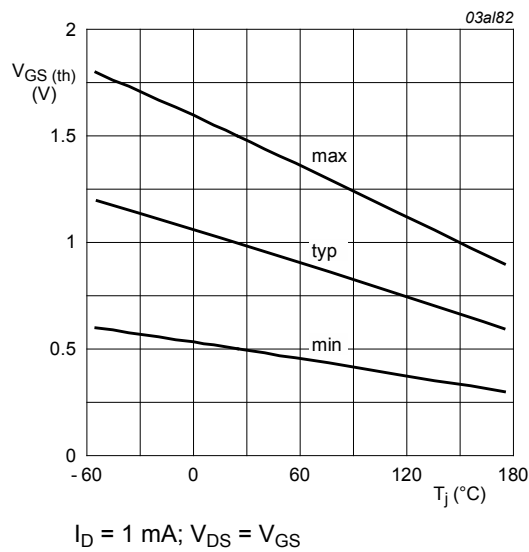


Fig. 13. Gate-source threshold voltage as a function of junction temperature

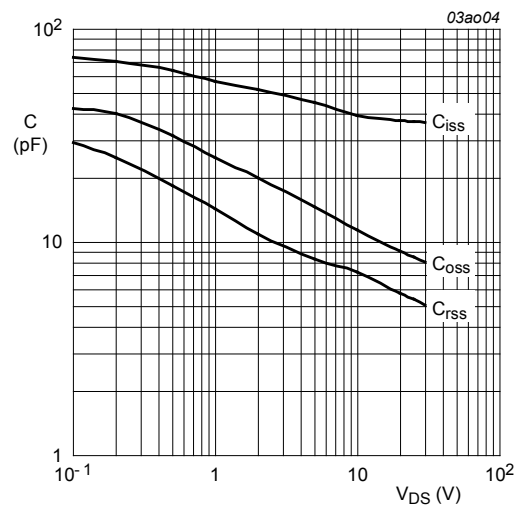


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

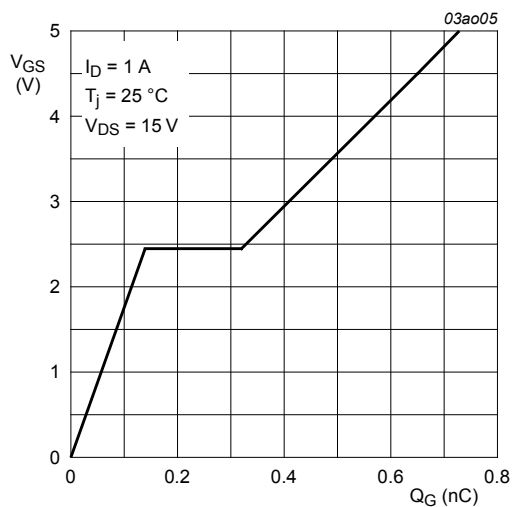


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$I_D = 1\text{ A}; V_{DS} = 15\text{ V}$

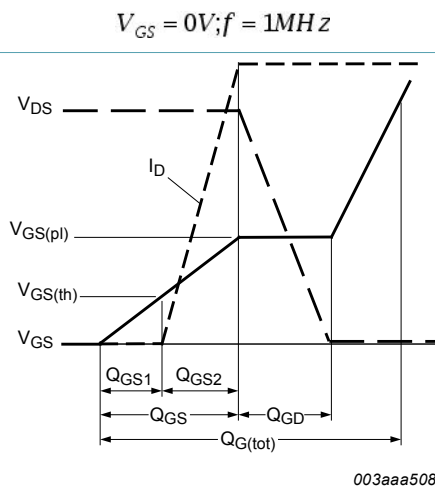
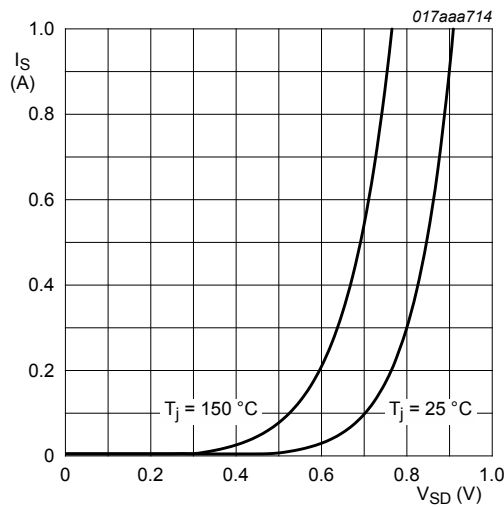


Fig. 16. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 17. Source current as a function of source-drain voltage; typical values

8. Test information

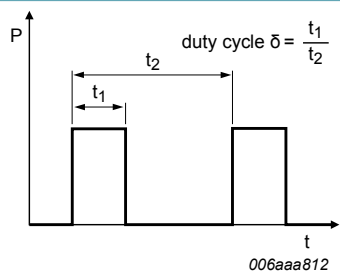


Fig. 18. Duty cycle definition

9. Package outline

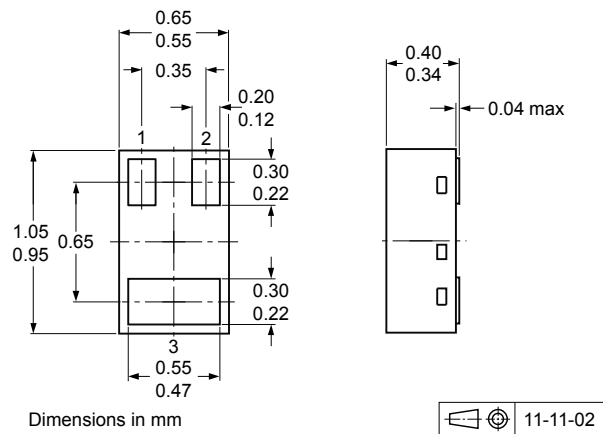


Fig. 19. DFN1006B-3 (SOT883B)



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### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## 13. Contents

<b>1</b>	<b>Product profile .....</b>	<b>1</b>
1.1	General description .....	1
1.2	Features and benefits .....	1
1.3	Applications .....	1
1.4	Quick reference data .....	1
<b>2</b>	<b>Pinning information .....</b>	<b>2</b>
<b>3</b>	<b>Ordering information .....</b>	<b>2</b>
<b>4</b>	<b>Marking .....</b>	<b>2</b>
<b>5</b>	<b>Limiting values .....</b>	<b>3</b>
<b>6</b>	<b>Thermal characteristics .....</b>	<b>4</b>
<b>7</b>	<b>Characteristics .....</b>	<b>5</b>
<b>8</b>	<b>Test information .....</b>	<b>9</b>
<b>9</b>	<b>Package outline .....</b>	<b>9</b>
<b>10</b>	<b>Soldering .....</b>	<b>10</b>
<b>11</b>	<b>Revision history .....</b>	<b>10</b>
<b>12</b>	<b>Legal information .....</b>	<b>11</b>
12.1	Data sheet status .....	11
12.2	Definitions .....	11
12.3	Disclaimers .....	11
12.4	Trademarks .....	12

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